Table of contents

- Preface to Third Edition
- 1 Resistivity
- 1.1 Introduction
- 1.2 Two-Point Versus Four-Point Probe
- 1.3 Wafer Mapping
- 1.4 Resistivity Profiling
- 1.5 Contactless Methods
- 1.6 Conductivity Type
- 1.7 Strengths and Weaknesses
- Appendix 1.1 Resistivity as a Function of Doping Density
- Appendix 1.2 Intrinsic Carrier Density
- References
- Problems
- Review Questions
- 2 Carrier and Doping Density
- 2.1 Introduction
- 2.2 Capacitance-Voltage (C-V)
- 2.3 Current-Voltage (I-V)
- 2.4 Measurement Errors and Precautions
- 2.5 Hall Effect
- 2.6 Optical Techniques
- 2.7 Secondary Ion Mass Spectrometry (SIMS)
- 2.8 Rutherford Backscattering (RBS)
- 2.9 Lateral Profiling
- 2.10 Strengths and Weaknesses
- Appendix 2.1 Parallel or Series Connection?
- Appendix 2.2 Circuit Conversion
- References
- Problems
- Review Questions
- 3 Contact Resistance and Schottky Barriers
- 3.1 Introduction
- 3.2 Metal-Semiconductor Contacts
- 3.3 Contact Resistance
- 3.4 Measurement Techniques
- 3.5 Schottky Barrier Height
- 3.6 Comparison of Methods
- 3.7 Strengths and Weaknesses
- Appendix 3.1 Effect of Parasitic Resistance
- Appendix 3.2 Alloys for Contacts to Semiconductors
- References
- Problems
- Review Questions
- 4 Series Resistance, Channel Length and Width, and Threshold Voltage

- 4.1 Introduction
- 4.2 PN Junction Diodes
- 4.3 Schottky Barrier Diodes
- 4.4 Solar Cells
- 4.5 Bipolar Junction Transistors
- 4.6 MOSFETS
- 4.7 MESFETS and MODFETS
- 4.8 Threshold Voltage
- 4.9 Pseudo MOSFET
- 4.10 Strengths and Weaknesses
- Appendix 4.1 Schottky Diode Current-Voltage Equation
- References
- Problems
- Review Questions
- 5 Defects
- 5.1 Introduction
- 5.2 Generation-Recombination Statistics
- 5.3 Capacitance Measurements
- 5.4 Current Measurements
- 5.5 Charge Measurements
- 5.6 Deep-Level Transient Spectroscopy (DLTS)
- 5.7 Thermally Stimulated Capacitance and Current
- 5.8 Positron Annihilation Spectroscopy (PAS)
- 5.9 Strengths and Weaknesses
- Appendix 5.1 Activation Energy and Capture Cross-Section
- Appendix 5.2 Time Constant Extraction
- Appendix 5.3 Si and GaAs Data
- References
- Problems
- Review Questions
- 6 Oxide and Interface Trapped Charges, Oxide Thickness
- 6.1 Introduction
- 6.2 Fixed, Oxide Trapped, and Mobile Oxide Charge
- 6.3 Interface Trapped Charge
- 6.4 Oxide Thickness
- 6.5 Strengths and Weaknesses
- Appendix 6.1 Capacitance Measurement Techniques
- Appendix 6.2 Effect of Chuck Capacitance and Leakage Current
- References
- Problems
- Review Questions
- 7 Carrier Lifetimes
- 7.1 Introduction
- 7.2 Recombination Lifetime/Surface Recombination Velocity
- 7.3 Generation Lifetime/Surface Generation Velocity
- 7.4 Recombination Lifetime-Optical Measurements

- 7.5 Recombination Lifetime-Electrical Measurements
- 7.6 Generation Lifetime-Electrical Measurements
- 7.7 Strengths and Weaknesses
- Appendix 7.1 Optical Excitation
- Appendix 7.2 Electrical Excitation
- References
- Problems
- Review Questions
- 8 Mobility
- 8.1 Introduction
- 8.2 Conductivity Mobility
- 8.3 Hall Effect and Mobility
- 8.4 Magnetoresistance Mobility
- 8.5 Time-of-Flight Drift Mobility
- 8.6 MOSFET Mobility
- 8.7 Contactless Mobility
- 8.8 Strengths and Weaknesses
- Appendix 8.1 Semiconductor Bulk Mobilities
- Appendix 8.2 Semiconductor Surface Mobilities
- Appendix 8.3 Effect of Channel Frequency Response
- Appendix 8.4 Effect of Interface Trapped Charge
- References
- Problems
- Review Questions
- 9 Charge-based and Probe Characterization
- 9.1 Introduction
- 9.2 Background
- 9.3 Surface Charging
- 9.4 The Kelvin Probe
- 9.5 Applications
- 9.6 Scanning Probe Microscopy (SPM
- 9.7 Strengths and Weaknesses
- References
- Problems
- Review Questions
- 10 Optical Characterization
- 10.1 Introduction
- 10.2 Optical Microscopy
- 10.3 Ellipsometry
- 10.4 Transmission
- 10.5 Reflection
- 10.6 Light Scattering
- 10.7 Modulation Spectroscopy
- 10.8 Line Width
- 10.9 Photoluminescence (PL
- 10.10 Raman Spectroscopy

- 10.11 Strengths and Weaknesses
- Appendix 10.1 Transmission Equations
- Appendix 10.2 Absorption Coefficients and Refractive Indices for SelectedSemiconductors
- References
- Problems
- Review Questions
- 11 Chemical and Physical Characterization
- 11.1 Introduction
- 11.2 Electron Beam Techniques
- 11.3 Ion Beam Techniques
- 11.4 X-Ray and Gamma-Ray Techniques
- 11.5 Strengths and Weaknesses
- Appendix 11.1 Selected Features of Some Analytical Techniques
- References
- Problems
- Review Questions
- 12 Reliability and Failure Analysis
- 12.1 Introduction
- 12.2 Failure Times and Acceleration Factors
- 12.3 Distribution Functions
- 12.4 Reliability Concerns
- 12.5 Failure Analysis Characterization Techniques
- 12.6 Strengths and Weaknesses
- Appendix 12.1 Gate Currents
- References
- Problems
- Review Questions
- Appendix 1 List of Symbols
- Appendix 2 Abbreviations and Acronyms
- Index